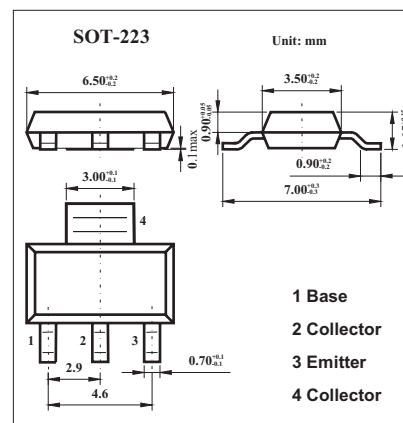


NPN Silicon Planar High Voltage Transistor

FZT458

■ Features

- 400 Volt V_{CE0}

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	300	A
Continuous Collector Current	I_C	1	A
Base Current	I_B	200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_J; T_{stg}$	-55 to +150	$^\circ\text{C}$

FZT458

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Max	Unit
Breakdown Voltages	V(BR)CBO	Ic=100μA	400		V
Breakdown Voltages	VCEO(sus)	Ic=10mA*	400		V
Breakdown Voltages	V(BR)EBO	Ie=100μA	5		V
Collector Cut-Off Currents	ICBO	VCB=320V		100	nA
	ICES	VCE=320V		100	nA
Emitter Cut-Off Current	IEBO	VEB=4V		100	nA
Emitter Saturation Voltages	VCE(sat)	Ic=20mA, Ib=2mA*		0.2	V
		Ic=50mA, Ib=6mA*		0.5	V
	VBE(sat)	Ic=50mA, Ib=5mA*		0.9	V
Base-Emitter Turn On Voltage	VBE(on)	Ic=50mA, VCE=10V*		0.9	V
Static Forward Current Transfer Ratio	hFE	Ic=1mA, VCE=10V	100		
		Ic=50mA, VCE=10V*	100	300	
		Ic=100mA, VCE=10V*	15		
Transition Frequency	fT	Ic=10mA, VCE=20V, f=20MHz			MHz
Collector-Base Breakdown Voltage	Cobo	VCB=20V, f=1MHz		5	pF
Switching times	ton	Ic=50mA, VCC=100V	135 Typical		ns
	toff	Ib1=5mA, Ib2=-10mA	2260 Typical		ns

* Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

■ Marking

Marking	FZT458
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